

File View Edit Tools Window Help

Close Minimize Maximize

Active

- ② L1: (155) (cell memory) near2 (area region section portion D)
- ② L2: (10053) cmos
- ② L3: (94) 1 and 2
- ② L4: (22678) pmos with nmos
- ② L5: (70) 3 and 4
- ② L6: (110) (257/214) CCLS

Failed

- ② Saved
- ② (1) 09/948877
- ② (1736) "KONINKLIJKE PHILIPS" as
- ② (2) 10/253779
- ② (1) 10/234501
- ② (37717) n-well pmos
- ② (43184) p-well nmos
- ② (1979052) peripher\$2 logic
- ② (2357117) cell memory
- ② (182171) (peripher\$2 logic 0) with (cell memory)
- ② (3810307) region area
- ② (82488) (cell memory) adj2 (region area)
- ② (7362802) (area region section portion)
- ② (215405) (cell memory) near2 (area region section portion D)
- ② (270282) (peripher\$2 logic 0) near2 (area region section portion D)
- ② (809848) polysilicon poly adj silicon silicon
- ② (3102552) metal

DBs: USPTO:US-PCPUB: EPO: JPO: DPERVENT: IBM: TDE

Default operator: OR

② Pixels

② Highlight cell features initially

10/253779

Feb. 2004

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U	I	Investor	Document	Issue	Title	Current	Current XN	Reviewed	S	C	P	Image	Doc	P
<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 2003008 2003012	CMOS of semiconductor device and method	f 257/389 257/E21.63	R	F	F	R	C	E	US 200300		
<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 6642132 200312	Cmos of semiconductor device and method	f 438/502 257/315	R	F	F	R	C	E	US 664213		

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